

Cypress Semiconductor Product Qualification Report

QTP# 024903 VERSION 4.0
January 2005

Synchronous SRAM Family	
Technology Derivative R7FT-3R, Fab4	
CY7C1354B CY7C1354BV25 CG6306BF	256K x 36 Pipelined SRAM with NoBL™ Architecture
CY7C1356B CY7C1356BV25	512K x 18 Pipelined SRAM with NoBL™ Architecture
CY7C1355B	256K x 36 Flow-through SRAM with NoBL™ Architecture
CY7C1357B	512K x 18 Flow-through SRAM with NoBL™ Architecture
CY7C1360B	256K x 36 Pipelined SRAM
CY7C1361B	256K x 36 Flow-through SRAM
CY7C1362B	512K x 18 Pipelined SRAM
CY7C1363B	512K x 18 Flow-through SRAM
CY7C1366B	256K x 36 Pipelined Double-Cycle Deselect SRAM
CY7C1367B	512K x 18 Pipelined Double-Cycle Deselect SRAM

CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

Sabbas Daniel
QA Engineering Director Sr.
(408) 943-2685

Mira Ben-Tzur
Reliability Engineer MTS
(408) 943-2675

PRODUCT QUALIFICATION HISTORY

Qual Report	Description of Qualification Purpose	Date Comp
014807	New Technology Derivative R7FT-3R / Synchronous Dual-Port RAM CY7C0852V, product family and package option.	Feb 02
012502	Device CY7C1360B and CY7C1354BV25 in Technology Derivative R7FT-3R, Fab 4	Apr 02
022610	Metal Mask change to enhance functionality to CY7C1360B/CY7C1361b/CY7C1366B	Oct 02
024605	New device CY7C1354B	Dec 02
024903	New device CY7C1356BV25, CY7C1356B and all the others of CY7C136*B RAM7	Dec 02
042305	R7FT-3R, 9 Meg Mask Fix for Glitch	Jul 04

Cypress products are manufactured using qualified processes. The technology qualification for this product is referenced above and must be considered to get a complete and thorough evaluation of the reliability of the product.

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualify CY7C13562BV25 in qualified technology Derivative R7FT-3R, Fab 4	
Marketing Part #:	CY7C1354B, CY7C1356B, CY7C1354BV25, CY7C1355B, CY7C1356BV25, CY7C1357B CY7C1360B, CY7C1361B CY7C1362B, CY7C1363B CY7C1366B/ CY7C1367B, CG6306BF
Device Description:	2.5V, 3.3V, Commercial and Industrial
Cypress Division:	Cypress Semiconductor Corporation –Memory Product Division (MPD)
Overall Die (or Mask) REV Level (pre-requisite for qualification):	Rev. B
What ID markings on Die:	7C13562B

TECHNOLOGY/FAB PROCESS DESCRIPTION – R7FT-3R			
Number of Metal Layers:	3	Metal Composition:	Metal 1: 150Å Ti / 4,200Å Al / 300Å TiW Metal 2: 150Å Ti / 4,200 Å Al / 300Å TiW Metal 3: 150Å Ti / 8,000Å Al / 300Å TiW
Passivation Type and Materials:	1000Å TEOS / 9000Å PECVD Nitride		
Free Phosphorus contents in top glass layer(%):	0%		
Number of Transistors in Device	60 million		
Number of Gates in Device	20 million		
Generic Process Technology/Design Rule (μ-drawn):	CMOS, Triple Metal /0.15 μm		
Gate Oxide Material/Thickness (MOS):	SiO ₂ , 32Å		
Name/Location of Die Fab (prime) Facility:	Cypress Semiconductor -- Bloomington, MN		
Die Fab Line ID/Wafer Process ID:	Fab4/R7FT-3R		

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY SITE FACILITY
119-ball BGA	ASE Taiwan
165-ball FBGA	ASE Taiwan
100-lead TQFP	CSPI-R / ASE Taiwan

Note: Package Qualification details upon request

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	A100
Package Outline, Type, or Name:	100-Thin Quad Flat Pack (TQFP)
Mold Compound Name/Manufacturer:	Hitachi CEL 9200
Mold Compound Flammability Rating:	V-O per UL94
Oxygen Rating Index:	>28%
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	Solder plate, 85%Sn, 15%Pb
Die Backside Preparation Method/Metallization:	N/A
Die Separation Method:	Wafer Saw
Die Attach Supplier:	Dexter
Die Attach Material:	QMI 509
Die Attach Method:	Epoxy
Bond Diagram Designation:	10-04943
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au, 1.0um
Thermal Resistance Theta JA °C/W:	41.7°C/W
Package Cross Section Yes/No:	N/A
Assembly Process Flow:	11-20030
Name/Location of Assembly (prime) facility:	Cypress Philippines (CML-R)

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	Cypress Philippines (CML-R)
Fault Coverage:	100%

Note: Please contact a Cypress Representative for other packages availability

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENT

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Vcc Max = 2.3V, 150°C	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc Max=2.3V, 150°C	P
High Temperature Steady State Life	Static Operating Condition, Vcc Max=3.63V, 150°C	P
High Accelerated Saturation Test (HAST)	130°C, 2.75V,85%RH 130°C, 3.63V,85%RH Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs, 30C/60%RH+3IR-Reflow, 220°C+5, 0°C	P
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs, 30C/60%RH+3IR-Reflow, 220°C+5, 0°C	P
Pressure Cooker	121°C, 100%RH Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs, 30C/60%RH+3IR-Reflow, 220°C+5, 0°C	P
High Temperature Storage	150°C ± 5°C no bias	P
Electrostatic Discharge Human Body Model (ESD-HBM)	2,200V MIL-STD-883, Method 3015.7	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V Cypress Spec. 25-00020	P
Current Density	Cypress Spec 22-00029	P
Age Bond Strength	200°C, 4HRS MIL-STD-883, Method 883-2011	P
Acoustic Microscopy, MSL 3	Cypress Spec. 25-00104	P
Dynamic Latchup	In accordance with JEDEC 17. Cypress Spec. 01-00081	P
Static Latchup	125C, 10V, ± 300mA In accordance with JEDEC 17. Cypress Spec. 01-00081	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF³	Failure Rate
High Temperature Operating Life Early Failure Rate	4,116	1	N/A	N/A	243 PPM
High Temperature Operating Life ^{1,2} Long Term Failure Rate	1,234,120 DHRs	0	0.7	170	4 FIT

¹ Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.

² Chi-squared 60% estimations used to calculate the failure rate..

³ Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A =The Activation Energy of the defect mechanism.

k = Boltzmann's constant = 8.62x10⁻⁵ eV/Kelvin.

T₁ is the junction temperature of the device under stress and T₂ is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #: 014807

Device	Fab Lot #	Assy Lot #	Ass Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL3							
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	COMP	15	0	
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	COMP	15	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	COMP	15	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2.3V, Vcc Max							
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	48	772	0	
CY7C0852V-BC(7C08523A)	4141878	610145152	ASE-TAIWN	96	455	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 2.3V, Vcc Max							
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	80	300	0	
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	500	274	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	80	400	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	500	193	0	
CY7C0852V-BC(7C08523A)	4133371	610137695	ASE-TAIWN	80	400	0	
CY7C0852V-BC(7C08523A)	4133371	610137695	ASE-TAIWN	500	385	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 1,100V							
CY7C0852V-BC(7C08523A)	4133371	610137695	ASE-TAIWN	COMP	9	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY7C0852V-BC(7C08523A)	4133371	610137695	ASE-TAIWN	COMP	9	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 10V, +/300mA							
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	COMP	3	0	
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	COMP	3	0	
STRESS: AGE BOND STRENGTH							
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	COMP	5	0	
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	COMP	6	0	
STRESS: HIGH TEMPERATURE STORAGE, PLASTIC, 150C							
CY7C0852V-BC(7C08523A)	4128335	610130788	ASE-TAIWN	500	48	0	
CY7C0852V-BC(7C08523A)	4128335	610130788	ASE-TAIWN	1000	48	0	

Reliability Test Data

QTP #: 014807

Device	Fab Lot #	Assy Lot #	Ass Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP STEADY STATE LIFE TEST, 150C, 3.63V, Vcc MAX							
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	80	78	0	
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	168	76	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH,, PRE COND 192 HR 30C/60%RH, MSL3							
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	168	47	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	168	48	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 3.63V, PRE COND 192 HR 30C/60%RH, MSL3							
CY7C0852V-BC(7C08523A)	4131840	610135256	ASE-TAIWN	128	48	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	128	46	0	
STRESS: TC COND. C -65C TO 150C, PRECONDITION 192 HRS 30C/60%RH, MSL3							
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	300	47	0	
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	500	46	0	
CY7C0852V-BC(7C08523A)	4130707	610133760L1	ASE-TAIWN	1000	45	0	
CY7C0852V-BC(7C08523A)	4131841	610137123L1	ASE-TAIWN	300	46	0	

Reliability Test Data

QTP #: 012502

Device	Fab Lot #	Assy Lot #	Ass Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL3							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	COMP	15	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	COMP	15	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	COMP	15	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2.3V, Vcc Max							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	36	500	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	36	988	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	36	1401	1	NON VISUAL
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 2.3V, Vcc Max							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	80	397	0	
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	500	382	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	80	398	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	500	398	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	80	795	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	500	794	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V							
CY7C1354BV25-AC (7C1354B)	4131928	610134485	CSPI-R	COMP	9	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	COMP	9	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY7C1354BV25-AC (7C1354B)	4131928	610134485	CSPI-R	COMP	9	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	COMP	9	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 10V, +/300mA							
CY7C1354BV25-AC (7C1354B)	4131928	610134485	CSPI-R	COMP	3	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	COMP	3	0	
STRESS: DYNAMIC LATCH-UP TESTING, 5.5V							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	COMP	15	0	
STRESS: AGE BOND STRENGTH							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	COMP	15	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	COMP	15	0	

Reliability Test Data

QTP #: 012502

Device	Fab Lot #	Assy Lot #	Ass Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMPERATURE STORAGE, PLASTIC, 150C							
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	500	48	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	1000	48	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST, 150C, 3.63V, Vcc MAX							
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	80	83	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	168	83	0	
STRESS: LOW TEMPERATURE OPERATING LIF,-30C, 3.25V							
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	500	47	0	
STRESS: TC COND. C -65C TO 150C, PRECONDITION 192 HRS 30C/60%RH, MSL3							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	300	47	0	
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	500	47	0	
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	1000	47	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	300	48	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	500	48	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	1000	48	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	300	50	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	500	50	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	1000	50	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH,, PRE COND 192 HR 30C/60%RH, MSL3							
CY7C1354BV25-AC (7C1354B)	4131928	610132955	CSPI-R	168	48	0	
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	168	48	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 2.75V, PRE COND 192 HR 30C/60%RH, MSL3							
CY7C1354BV25-AC (7C1354B)	4132009	610137503	CSPI-R	128	48	0	
CY7C1354BV25-AC (7C1354B)	4134403	610144437	CSPI-R	128	46	0	

Reliability Test Data

QTP #: 022610

Device	Fab Lot #	Assy Lot #	Ass Loc	Duration	Samp	Rej	Failure Mechanism
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STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2.3V, Vcc Max

CY7C1354BV25-AC (7C13542B)	4220687	610239285	CSPI-R	48	1777	0	
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STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V

CY7C1354BV25-AC (7C13542B)	4220687	610239285	CSPI-R	COMP	9	0	
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STRESS: ESD-CHARGE DEVICE MODEL, 500V

CY7C1354BV25-AC (7C13542B)	4220687	610239285	CSPI-R	COMP	9	0	
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STRESS: STATIC LATCH-UP TESTING, 125C, 10V, +/-300Ma

CY7C1354BV25-AC (7C13542B)	4220687	610239285	CSPI-R	COMP	3	0	
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Reliability Test Data

QTP #: 024903

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Ass Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
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STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V

CY7C13562BV25-AC (7C13562B)	4220626	610248377	CMLR	COMP	9	0	
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STRESS: ESD-CHARGE DEVICE MODEL, 500V

CY7C13562BV25-AC (7C13562B)	4220626	610248377	CMLR	COMP	9	0	
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STRESS: STATIC LATCH-UP TESTING, 125C, 10V, +/300mA

CY7C13562BV25-AC (7C13562B)	4220626	610248377	CMLR	COMP	3	0	
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Reliability Test Data

QTP #: 042305

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Ass Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
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STRESS: ESD-CHARGE DEVICE MODEL, 500V

CY7C1360B (7C13600R)	4413001	610431305	CML-R	COMP	9	0	
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STRESS: ESD-HUMAN BODY CIRCUIT PER JESD22, METHOD A114-B, 2,200V

CY7C1360B (7C13600R)	4413001	610431305	CML-R	COMP	9	0	
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STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V

CY7C1360B (7C13600R)	4413001	610431305	CML-R	COMP	3	0	
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STRESS: STATIC LATCH-UP TESTING, 125C, 7.5V, +/-300mA

CY7C1360B (7C13600R)	4413001	610431305	CML-R	COMP	3	0	
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